

### Höchstzulässige Werte / Maximum rated values

#### Elektrische Eigenschaften / Electrical properties

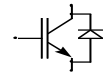
Kollektor-Emitter-Sperrspannung collector-emitter voltage		$V_{CES}$	1700	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^\circ\text{C}$	$I_{C,nom.}$	150	A
	$T_C = 25^\circ\text{C}$	$I_C$	300	A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 80^\circ\text{C}$	$I_{CRM}$	300	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^\circ\text{C}$ , Transistor	$P_{tot}$	1250	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		$V_{GES}$	+/- 20V	V
Dauergleichstrom DC forward current		$I_F$	150	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	$I_{FRM}$	300	A
Grenzlastintegral der Diode $I^2t$ - value, Diode	$V_R = 0\text{V}, t_p = 10\text{ms}, T_{vj} = 125^\circ\text{C}$	$I^2t$	4.500	$\text{A}^2\text{s}$
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{ Hz}, t = 1\text{ min.}$	$V_{ISOL}$	3,4	kV

### Charakteristische Werte / Characteristic values

#### Transistor / Transistor

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 150\text{A}, V_{GE} = 15\text{V}, T_{vj} = 25^\circ\text{C}$	$V_{CE\text{ sat}}$	-	2,6	3,2	V
	$I_C = 150\text{A}, V_{GE} = 15\text{V}, T_{vj} = 125^\circ\text{C}$		-	3,1	3,6	V
Gate-Schwellenspannung gate threshold voltage	$I_C = 7\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^\circ\text{C}$	$V_{GE(th)}$	4,5	5,5	6,5	V
Gateladung gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$	$Q_G$	-	1,8	-	$\mu\text{C}$
Eingangskapazität input capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	$C_{ies}$	-	10	-	nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	$C_{res}$	-	0,5	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^\circ\text{C}$	$I_{CES}$	-	0,05	0,3	mA
	$V_{CE} = 1700\text{V}, V_{GE} = 0\text{V}, T_{vj} = 125^\circ\text{C}$		-	4		mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^\circ\text{C}$	$I_{GES}$	-	-	200	nA

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**Charakteristische Werte / Characteristic values**

**Transistor / Transistor**

**min. typ. max.**

Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = 150A, V_{CE} = 900V$	$t_{d,on}$	-	0,1	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 125^\circ C$					
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 150A, V_{CE} = 900V$	$t_r$	-	0,1	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 125^\circ C$					
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = 150A, V_{CE} = 900V$	$t_{d,off}$	-	0,8	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 125^\circ C$					
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 150A, V_{CE} = 900V$	$t_f$	-	0,03	-	$\mu s$
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 10\Omega, T_{vj} = 125^\circ C$					
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 150A, V_{CE} = 900V, V_{GE} = 15V$ $R_G = 10\Omega, T_{vj} = 125^\circ C, L_S = 60nH$	$E_{on}$	-	70	-	mWs
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 150A, V_{CE} = 900V, V_{GE} = 15V$ $R_G = 10\Omega, T_{vj} = 125^\circ C, L_S = 60nH$	$E_{off}$	-	46	-	mWs
Kurzschlußverhalten SC Data	$t_p \leq 10\mu sec, V_{GE} \leq 15V$ $T_{vj} \leq 125^\circ C, V_{CC} = 1000V, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$I_{SC}$	-	600	-	A
Modulinduktivität stray inductance module		$L_{sCE}$	-	30	-	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	pro Zweig / per arm	$R_{CC+EE}$	-	0,6	-	m $\Omega$

**Charakteristische Werte / Characteristic values**

**Diode / Diode**

**min. typ. max.**

Durchlaßspannung forward voltage	$I_F = 150A, V_{GE} = 0V, T_{vj} = 25^\circ C$	$V_F$	-	2,1	2,5	V
	$I_F = 150A, V_{GE} = 0V, T_{vj} = 125^\circ C$					
Rückstromspitze peak reverse recovery current	$I_F = 150A, -di_F/dt = 1700A/\mu sec$	$I_{RM}$	-	110	-	A
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$					
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$					
Sperrverzögerungsladung recovered charge	$I_F = 150A, -di_F/dt = 1700A/\mu sec$	$Q_r$	-	35	-	$\mu As$
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$					
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$					
Abschaltenergie pro Puls reverse recovery energy	$I_F = 150A, -di_F/dt = 1700A/\mu sec$	$E_{rec}$	-	15	-	mWs
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 25^\circ C$					
	$V_R = 900V, V_{GE} = -10V, T_{vj} = 125^\circ C$					